

11. (Amended) A polishing method according to claim 17, wherein said second polishing liquid does not contain abrasive grains.

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12. (Amended) A polishing method according to claim 17, wherein said Ru compound is SrRuO_3 .

-- 17. (New) A polishing method comprising:

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preparing a first polishing liquid containing trivalent cerium ions in a first concentration;

adding a solvent to said first polishing liquid to form a second polishing liquid containing tetravalent cerium ions in a second concentration lower than the first concentration;

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polishing a surface of a substrate containing Ru or a Ru compound in a surface region with the second polishing liquid,

wherein said addition of the solvent is carried out upon or immediately before the polishing of said substrate.

18. (New) A polishing method according to claim 17, wherein said second polishing liquid contains cerium (IV) nitrate in a concentration of 0.75% or more by weight.

19. (New) A polishing method according to claim 18, wherein said second polishing liquid contains cerium (IV) nitrate in a concentration of 0.75 to 2% by weight.

20. (New) A polishing method according to claim 17, wherein said second polishing liquid contains diammonium cerium (IV) nitrate in a concentration of 3% or more by weight.

21. (New) A polishing method according to claim 20, wherein said second polishing liquid contains diammonium cerium (IV) nitrate in a concentration of 3 to 8% by weight.

Sub 22. (New) A polishing method comprising:

preparing a first polishing liquid containing cerium (IV) nitrate in a first concentration;

adding a solvent to said first polishing liquid to form a second polishing liquid containing cerium (IV) nitrate in a second concentration lower than the first concentration;

polishing a surface of a substrate containing Ru or a Ru compound in a surface region with the second polishing liquid,

wherein said adding of the solvent is carried out upon or immediately before the polishing of said substrate. - -

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